

# **Medium Power Thyristors**

## (Stud Version), 16 A



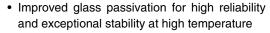
TO-208AA (TO-48)

16 A

**PRODUCT SUMMARY** 

 $I_{T(AV)}$ 

### **FEATURES**





- · High dl/dt and dV/dt capabilities
- · Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- · RoHS compliant
- Designed and qualified for industrial and consumer level

### **TYPICAL APPLICATIONS**

- · Medium power switching
- · Phase control applications
- · Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
		16	A		
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		35	A		
1	50 Hz	340	A		
I <sub>TSM</sub>	60 Hz	360	A		
l <sup>2</sup> t	50 Hz	574	A <sup>2</sup> s		
	60 Hz	524	A-5		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
tq	Typical	110	μs		
T <sub>J</sub>		- 65 to 125	°C		

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### **16RIA Series**

Vishay Semiconductors

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### **ELECTRICAL SPECIFICATIONS**

VOLTAGI	VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
16RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### Notes

 $<sup>\</sup>ensuremath{^{(2)}}$  For voltage pulses with  $t_p \leq 5 \mbox{ ms}$ 

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	I <sub>T(AV)</sub>	180° sinusoidal conduction		16 85	A °C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>				35	A
Maximum peak, one-cycle non-repetitive surge current	, ,	t = 10 ms	No voltage		340	
		t = 8.3 ms reapplied		360	^	
	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal	285	A
		t = 8.3 ms	reapplied	half wave,	300	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	initial T <sub>J</sub> =	574	
	l <sup>2</sup> t	t = 8.3 ms reapplied	T <sub>J</sub> maximum	524	A <sup>2</sup> s	
		t = 10 ms	100 % V <sub>RRM</sub>		405	A-S
		t = 8.3 ms	reapplied		375	
Maximum $I^2\sqrt{t}$ for fusing	I²√t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		5740	A²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		0.97	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(A)})$	$()$ , $T_J = T_J$ maxim	num	1.24	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $ _{T(AV)} < I < \pi$ x $ _{T(AV)}$ ), T <sub>J</sub> = T <sub>J</sub> maximum		17.9	<b></b> 0	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.6	mΩ	
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 50 A, T <sub>J</sub> = 25 °C		1.75	V	
Maximum holding current	I <sub>H</sub>			130	no A	
Latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 6 V, resistive load			200	mA

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs





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SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise	V <sub>DRM</sub> ≤ 800 V	dl/dt	$T_J = T_J \text{ maximum, } V_{DM} = \text{Rated } V_{DRM}$		A /
of turned-on current $V_{DRM} \le$	$V_{DRM} \le 1000 \text{ V}$	ui/ut	Gate pulse = 20 V, 15 $\Omega$ , $t_p$ = 6 $\mu$ s, $t_r$ = 0.1 $\mu$ s maximum $I_{TM}$ = (2 x rated dI/dt) A	160	A/μs
V <sub>DRM</sub> ≤ 1600 V		Tim (2 × races analy r		150	
Typical turn-on time		t <sub>gt</sub>	$T_J = 25 ^{\circ}\text{C}$ , at rated $V_{DRM}/V_{RRM}$ , $T_J = 125 ^{\circ}\text{C}$	0.9	
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \ \mu s$ , $dI/dt = -10 \ A/\mu s$	4	μs
Typical turn-off time		tq	$T_J = T_J \text{ maximum, } I_{TM} = I_{T(AV)}, t_p > 200 \mu\text{s, } V_R = 100 V,$ $dI/dt = \text{- 10 A/}\mu\text{s, } dV/dt = 20 V/\mu\text{s linear to 67 \% V}_{DRM},$ gate bias 0 V to 100 W	110	

#### Note

-  $t_q$  = 10  $\mu s$  up to 600 V,  $t_q$  = 30  $\mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	100	V/µs
of off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated $V_{DRM}$	300 (1)	ν/μδ

### Note

 $^{(1)}$  Available with: dV/dt = 1000 V/ $\mu$ s, to complete code add S90 i.e. 16RIA120S90

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	T. T. manifesture		8.0	W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum		2.0	VV
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
		T <sub>J</sub> = - 65 °C	Maximum required gate trigger	90	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	60	mA
		T <sub>J</sub> = 125 °C		35	
		T <sub>J</sub> = - 65 °C		3.0	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		2.0	V
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	I <sub>GD</sub>	$T_J = T_J \text{ maximum}, V_{DRM} = \text{Rated value}$		2.0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	>

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 125		°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	UC DC operation		0.86		
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.35		K/W	
			TO NUT	TO DEVICE		
			20 (27.5)	25	lbf ⋅ in	
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m	
		(Non labilitation timeday)	2.3 (3.1)	2.8	N · m	
Approximate weight			1	4	g	
Approximate weight	Approximate weight		0.	49	OZ.	
Case style		See dimensions - link at the end of datasheet TO-208AA (TO-4		208AA (TO-48	)	

△R <sub>thJC</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.21	0.15					
120°	0.25	0.25					
90°	0.31	0.34	$T_J = T_J \text{ maximum}$	K/W			
60°	0.45	0.47					
30°	0.76	0.76					

#### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

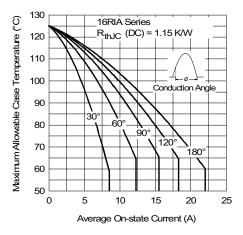


Fig. 1 - Current Ratings Characteristics

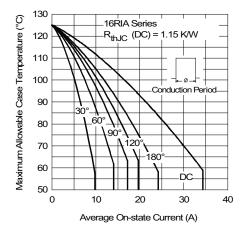


Fig. 2 - Current Ratings Characteristics



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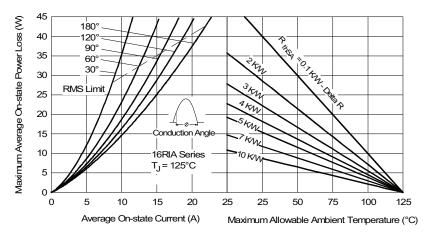


Fig. 3 - On-State Power Loss Characteristics

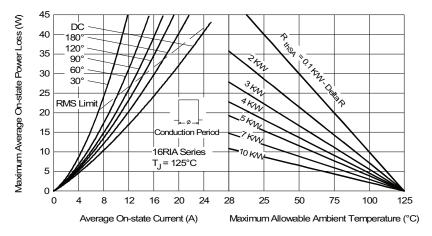


Fig. 4 - On-State Power Loss Characteristics

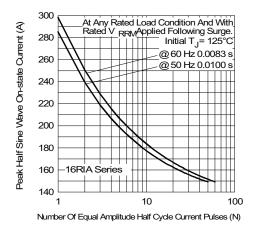


Fig. 5 - Maximum Non-Repetitive Surge Current

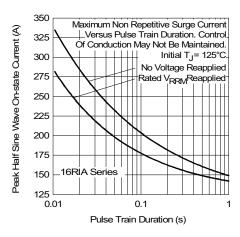


Fig. 6 - Maximum Non-Repetitive Surge Current

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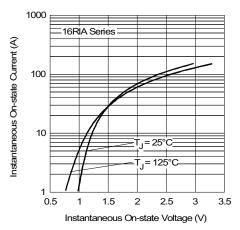


Fig. 7 - Forward Voltage Drop Characteristics

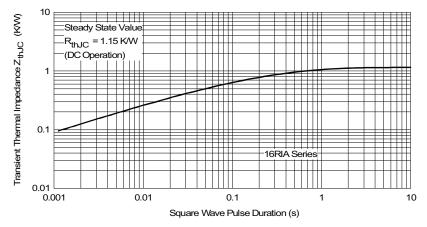


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

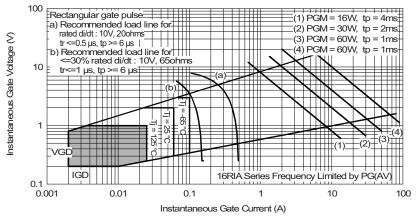


Fig. 9 - Gate Characteristics



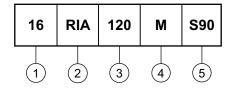


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### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Current code
- 2 Essential part number
- 3 Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)
- None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
   M = Stud base TO-208AA (TO-48) M6 x 1
- 5 Critical dV/dt:
  None = 300 V/µs (standard value)
  S90 = 1000 V/µs (special selection)

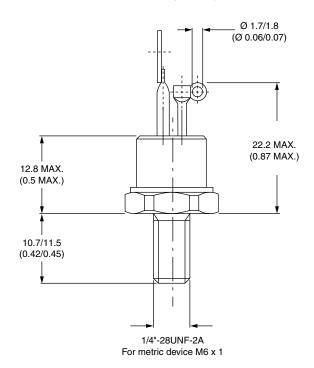
LINKS TO RELATED DOCUMENTS			
Dimensions	http://www.vishay.com/doc?95333		

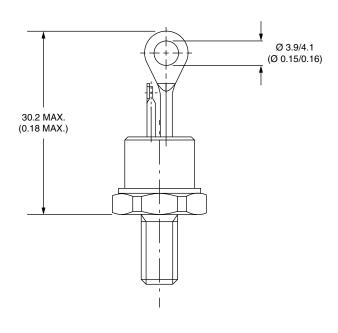
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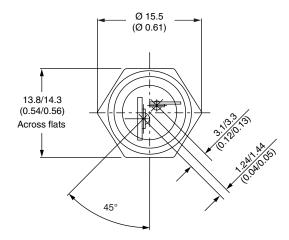


## TO-208AA (TO-48)

### **DIMENSIONS** in millimeters (inches)









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